TOSHIBA Photocoupler GaAℓAs Ired & Photo−IC

TLP250

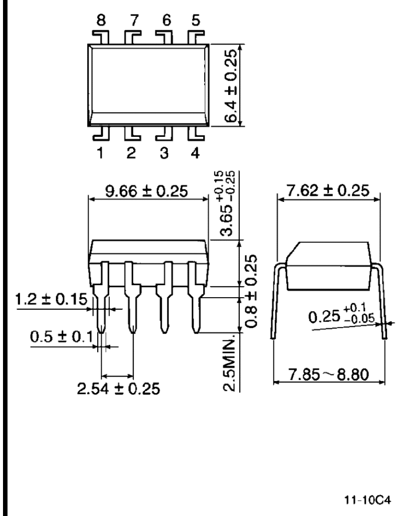
Transistor Inverter
Inverter For Air Conditionor
IGBT Gate Drive
Power MOS FET Gate Drive

The TOSHIBA TLP250 consists of a GaAlAs light emitting diode and a integrated photodetector.
This unit is 8−lead DIP package.
TLP250 is suitable for gate driving circuit of IGBT or power MOS FET.

- Input threshold current: I_F=5mA(max.)
- Supply current (I_{CC}): 11mA(max.)
- Supply voltage (V_{CC}): 10−35V
- Output current (I_O): ±1.5A (max.)
- Switching time (t_{pLH}/t_{pHL}): 1.5μs(max.)
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: UL1577, file No.E67349
- Option(D4)
  VDE Approved : DIN EN60747-5-2
  Maximum Operating Insulation Voltage : 890V_{PK}
  Highest Permissible Over Voltage : 4000V_{PK}

**(Note):When a EN60747-5-2 approved type is needed,
Please designate "Option(D4)"**

Unit in mm



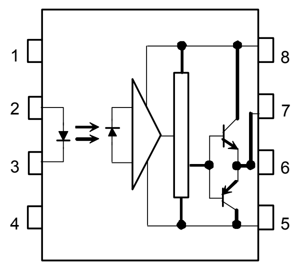
TOSHIBA 11−10C4

Weight: 0.54 g(Typ.)

Truth Table

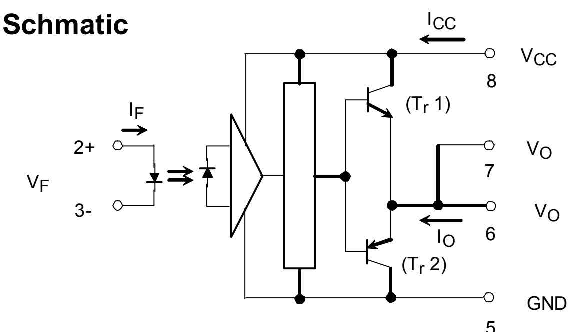
		Tr1	Tr2
Input LED	On	On	Off
	Off	Off	On

Pin Configuration (top view)



1 : N.C.	5 : GND
2 : Anode	6 : V_O (Output)
3 : Cathode	7 : V_O
4 : N.C.	8 : V_{CC}

Schmatic



A 0.1μF bypass capcitor must be connected between pin 8 and 5 (See Note 5).

Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
LED	Forward current		I_F	20	mA
	Forward current derating (Ta ≥ 70°C)		ΔI_F / ΔTa	−0.36	mA / °C
	Peak transient forward curent (Note 1)		I_{FPT}	1	A
	Reverse voltage		V_R	5	V
	Junction temperature		Tj	125	°C
Detector	"H"peak output current (P_W ≤ 2.5μs,f ≤ 15kHz) (Note 2)		I_{OPH}	−1.5	A
	"L"peak output current (P_W ≤ 2.5μs,f ≤ 15kHz) (Note 2)		I_{OPL}	+1.5	A
	Output voltage	(Ta ≤ 70°C)	V_O	35	V
		(Ta = 85°C)		24	
	Supply voltage	(Ta ≤ 70°C)	V_{CC}	35	V
		(Ta = 85°C)		24	
	Output voltage derating (Ta ≥ 70°C)		ΔV_O / ΔTa	−0.73	V / °C
	Supply voltage derating (Ta ≥ 70°C)		ΔV_{CC} / ΔTa	−0.73	V / °C
	Junction temperature		Tj	125	°C
Operating frequency (Note 3)			f	25	kHz
Operating temperature range			T_{opr}	−20~85	°C
Storage temperature range			T_{stg}	−55~125	°C
Lead soldering temperature (10 s)			T_{sol}	260	°C
Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 4)			BV_S	2500	Vrms

Note 1: Pulse width P_W ≤ 1μs, 300pps

Note 2: Exporenential wavefom

Note 3: Exporenential wavefom, I_{OPH} ≤ −1.0A(≤ 2.5μs), I_{OPL} ≤ +1.0A(≤ 2.5μs)

Note 4: Device considerd a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Note 5: A ceramic capacitor(0.1μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching proparty. The total lead length between capacitor and coupler should not exceed 1cm.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max		Unit
Input current, on (Note6)	$I_{F(ON)}$	7	8	10		mA
Input voltage, off	$V_{F(OFF)}$	0	—	0.8		V
Supply voltage	V_{CC}	15	—	30	20	V
Peak output current	I_{OPH}/I_{OPL}	—	—	±0.5		A
Operating temperature	T_{opr}	−20	25	70	85	°C

Note 6: Input signal rise time(fall time)<0.5μs.

Electrical Characteristics (Ta = −20~70°C, unless otherwise specified)

Characteristic		Symbol	Test Circuit	Test Condition		Min	Typ.*	Max	Unit
Input forward voltage		V_F	—	I_F = 10 mA , Ta = 25°C		—	1.6	1.8	V
Temperature coefficient of forward voltage		$\Delta V_F / \Delta Ta$	—	I_F = 10 mA		—	−2.0	—	mV / °C
Input reverse current		I_R	—	V_R = 5V, Ta = 25°C		—	—	10	μA
Input capacitance		C_T	—	V = 0 , f = 1MHz , Ta = 25°C		—	45	250	pF
Output current	"H" level	I_{OPH}	1	V_{CC} = 30V (*1)	I_F = 10 mA, V_{8-6} = 4V	−0.5	−1.5	—	A
	"L" level	I_{OPL}	2		I_F = 0, V_{6-5} = 2.5V	0.5	2	—	
Output voltage	"H" level	V_{OH}	3	V_{CC1} = +15V, V_{EE1} = −15V, R_L = 200Ω, I_F = 5mA		11	12.8	—	V
	"L" level	V_{OL}	4	V_{CC1} = +15V, V_{EE1} = −15V, R_L = 200Ω, V_F = 0.8V		—	−14.2	−12.5	
Supply current	"H" level	I_{CCH}	—	V_{CC} = 30V, I_F = 10mA, Ta = 25°C		—	7	—	mA
				V_{CC} = 30V, I_F = 10mA		—	—	11	
	"L" level	I_{CCL}	—	V_{CC} = 30V, I_F = 0mA, Ta = 25°C		—	7.5	—	
				V_{CC} = 30V, I_F = 0mA		—	—	11	
Threshold input current	"Output L→H"	I_{FLH}	—	V_{CC1} = +15V, V_{EE1} = −15V, R_L = 200Ω, V_O > 0V		—	1.2	5	mA
Threshold input voltage	"Output H→L"	V_{FHL}	—	V_{CC1} = +15V, V_{EE1} = −15V, R_L = 200Ω, V_O < 0V		0.8	—	—	V
Supply voltage		V_{CC}	—			10	—	35	V
Capacitance (input−output)		C_S	—	V_S = 0 , f = 1MHz, Ta = 25°C		—	1.0	2.0	pF
Resistance(input−output)		R_S	—	V_S = 500V , Ta = 25°C, R.H.≤ 60%		1×10^{12}	10^{14}	—	Ω

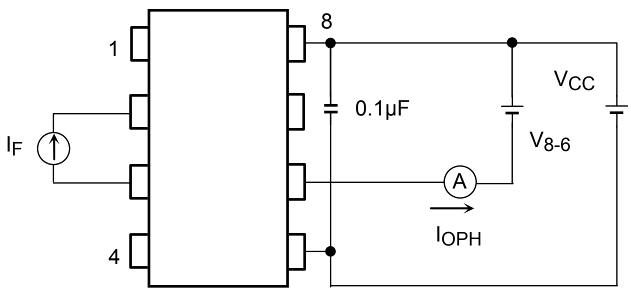
* All typical values are at Ta = 25°C (*1): Duration of I_O time ≤ 50μs

Switching Characteristics (Ta = −20~70°C , unless otherwise specified)

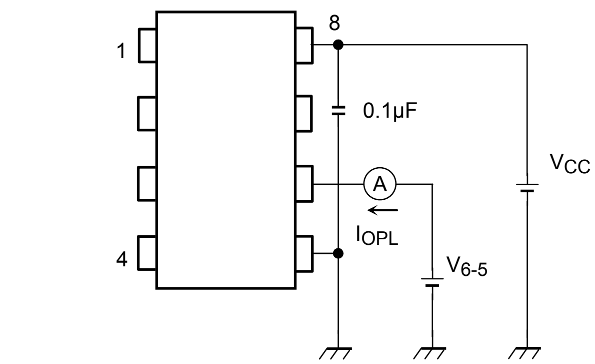
Characteristic		Symbol	Test Cir−cuit	Test Condition	Min	Typ.*	Max	Unit
Propagation delay time	L→H	t_{pLH}	5	I_F = 8mA V_{CC1} = +15V, V_{EE1} = −15V R_L = 200Ω	—	0.15	0.5	μs
	H→L	t_{pHL}			—	0.15	0.5	
Output rise time		t_r			—	—	—	
Output fall time		t_f			—	—	—	
Common mode transient immunity at high level output		C_{MH}	6	V_{CM} = 600V, I_F = 8mA V_{CC} = 30V, Ta = 25°C	−5000	—	—	V / μs
Common mode transient immunity at low level output		C_{ML}		V_{CM} = 600V, I_F = 0mA V_{CC} = 30V, Ta = 25°C	5000	—	—	V / μs

All typical values are at Ta = 25°C

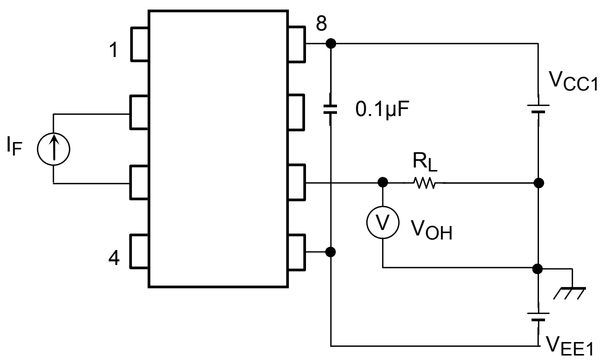
Test Circuit 1 : I_{OPH}



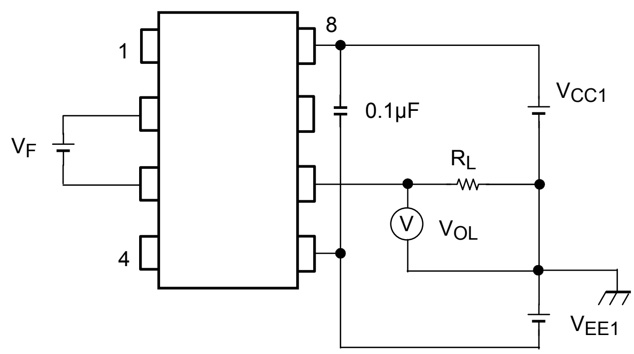
Test Circuit 2 : I_{OPL}



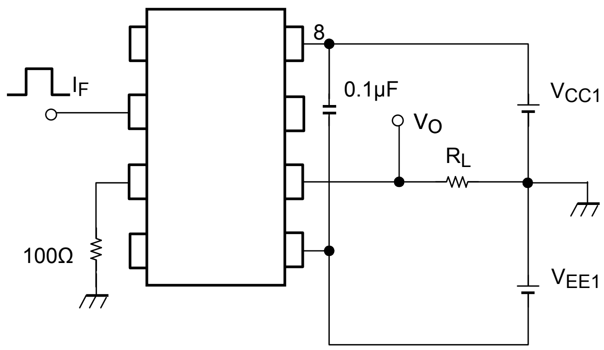
Test Circuit 3 : V_{OH}

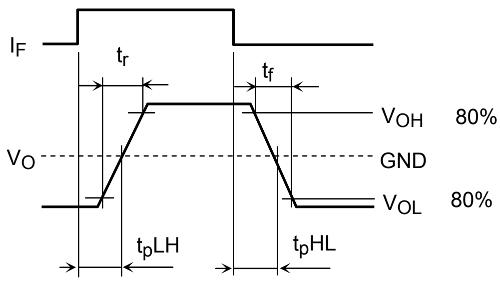


Test Circuit 4 : V_{OL}

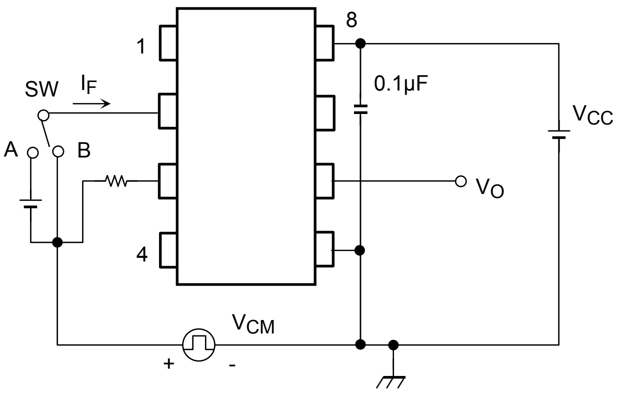


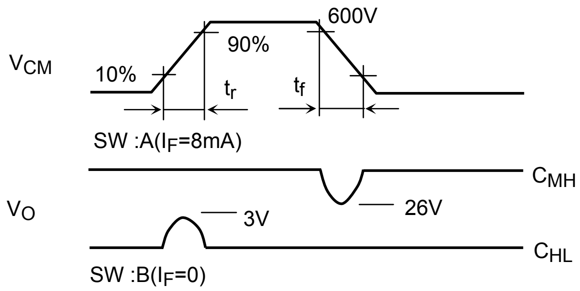
Test Circuit 5: t_{pLH}, t_{pHL}, t_r t_f





Test Circuit 6: C_{MH}, C_{ML}

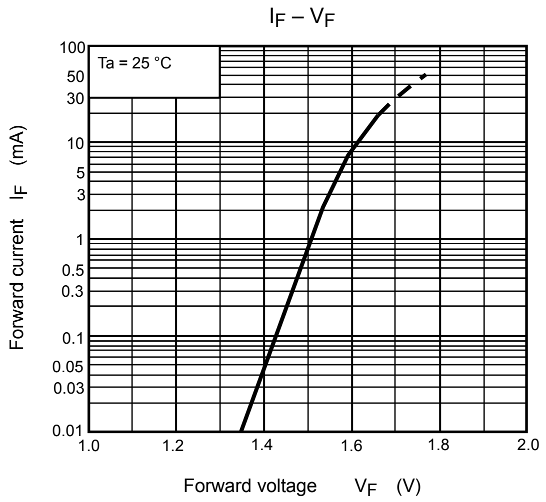


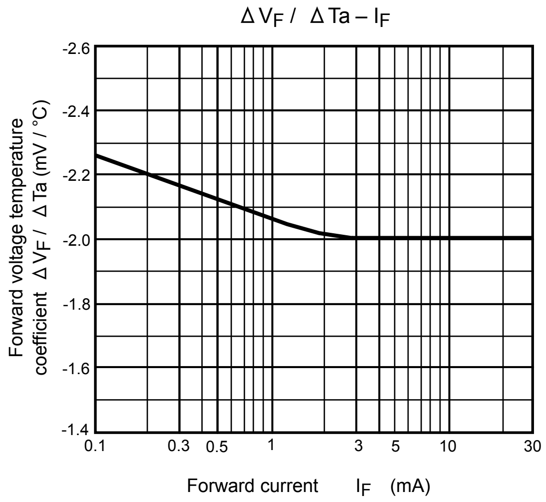


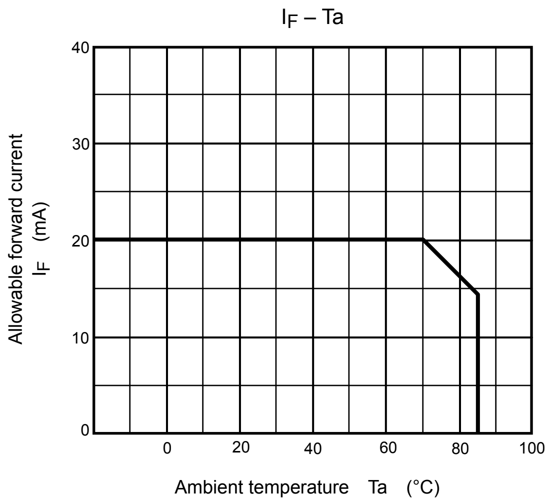
$$C_{ML} = \frac{480\ (V)}{t_{r\ (\mu s)}}$$

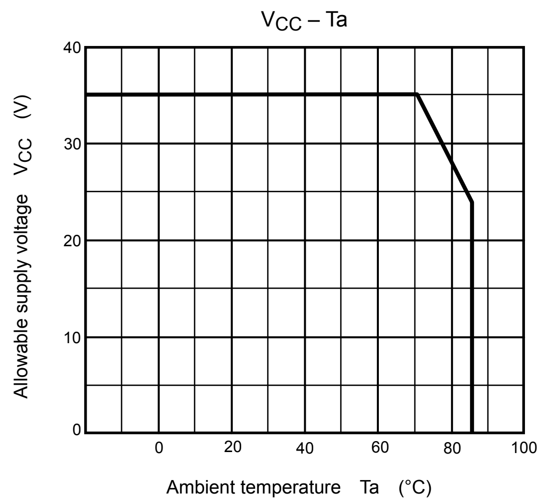
$$C_{MH} = \frac{480\ (V)}{t_{f\ (\mu s)}}$$

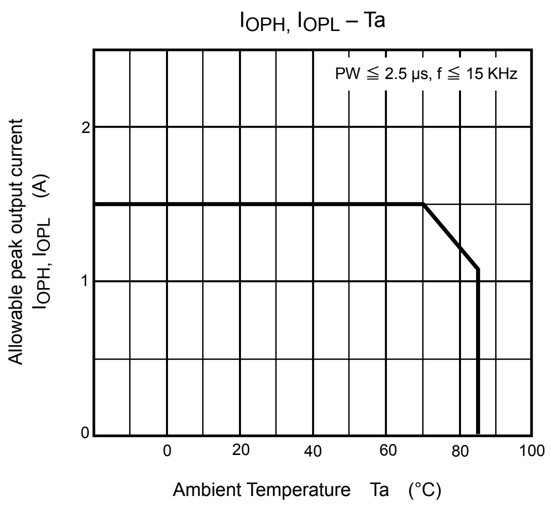
C_{ML}(C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.


IF – VF
Ta = 25 °C
Forward current IF (mA)
Forward voltage VF (V)
100
50
30
10
5
3
1
0.5
0.3
0.1
0.05
0.03
0.01
1.0
1.2
1.4
1.6
1.8
2.0


Δ VF / Δ Ta – IF
Forward voltage temperature coefficient Δ VF / Δ Ta (mV / °C)
Forward current IF (mA)
-2.6
-2.4
-2.2
-2.0
-1.8
-1.6
-1.4
0.1
0.3
0.5
1
3
5
10
30


IF – Ta
Allowable forward current IF (mA)
Ambient temperature Ta (°C)
40
30
20
10
0
0
20
40
60
80
100


VCC – Ta
Allowable supply voltage VCC (V)
Ambient temperature Ta (°C)
40
30
20
10
0
0
20
40
60
80
100


IOPH, IOPL – Ta
PW ≦ 2.5 μs, f ≦ 15 KHz
Allowable peak output current IOPH, IOPL (A)
Ambient Temperature Ta (°C)
2
1
0
0
20
40
60
80
100

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20070701-EN

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